

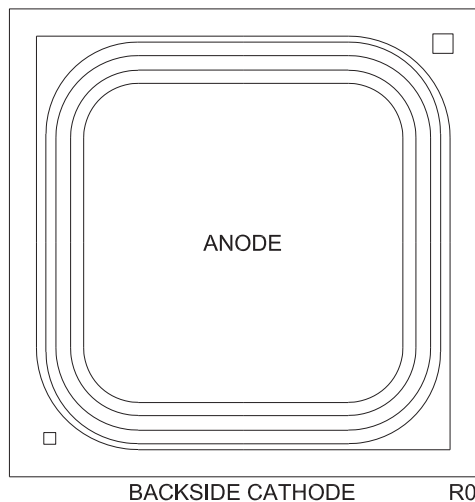
PROCESS CPD104R
Schottky Diode
Low VF Schottky Diode Chip



PROCESS DETAILS

Die Size	14.6 x 14.6 MILS
Die Thickness	3.9 MILS
Anode Bonding Pad Area	11.8 x 11.8 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



GROSS DIE PER 5 INCH WAFER

80,698

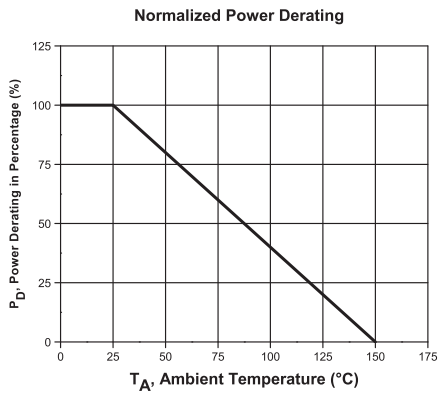
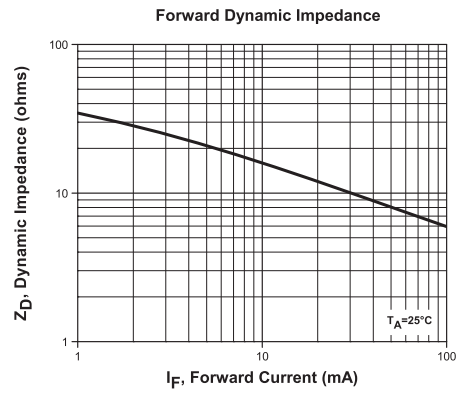
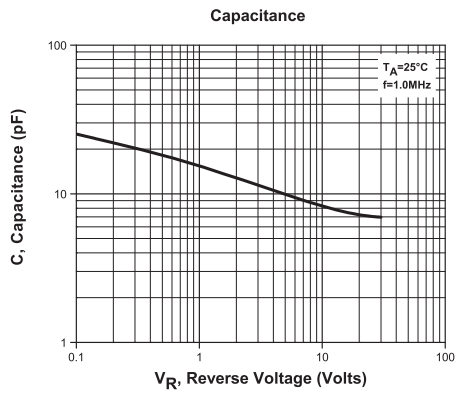
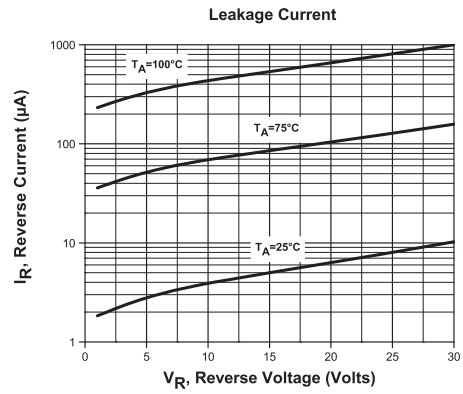
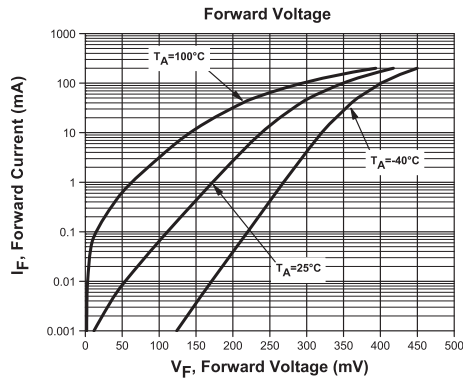
PRINCIPAL DEVICE TYPES

CFSH2-3L

R0 (1-February 2011)

PROCESS CPD104R

Typical Electrical Characteristics



R0 (1-February 2011)